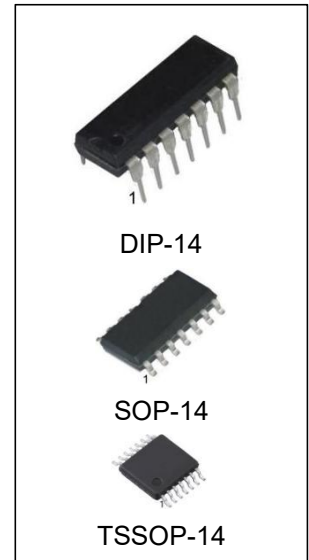


## CMOS Dual Complementary Pair Plus Inverter

### Features

- High-Voltage Type (15V Rating)
- Standardized Symmetrical Output Characteristics
- Medium Speed Operation:  $t_{PHL}, t_{PLH} = 30 \text{ ns (typ)}$  at 10V
- 100% Tested for Maximum Quiescent Current at 15V
- Meets All Requirements of JEDEC Tentative Standards No.13B, "Standard Specifications for Description of "B" Series CMOS Devices"
- Maximum Input Current of  $1\mu\text{A}$  at 15V Over Full Package-Temperature Range;  $100\text{nA}$  at 15V and  $+25^\circ\text{C}$



### Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
CD4007UBE/ CD4007UBN	DIP-14	CD4007UB	TUBE	1000pcs/Box
CD4007UBM/TR	SOP-14	CD4007UB	REEL	2500pcs/Reel
CD4007UBMT/TR	TSSOP-14	CD4007UB	REEL	2500pcs/Reel

## Description

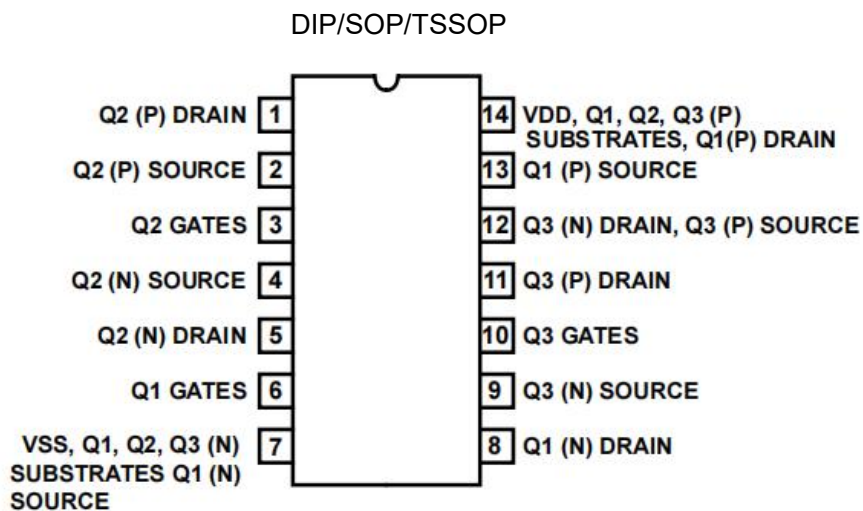
CD4007UB types are comprised of three n-channel and three p-channel enhancement-type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in Figure 2.

More complex functions are possible using multiple packages. Numbers shown in parentheses indicate terminals that are connected together to form the various configurations listed.

## Applications

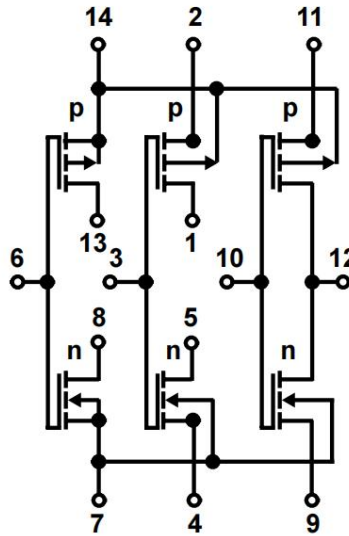
- Extremely High-Input Impedance Amplifiers
- Shapers
- Inverters
- Threshold Detector
- Linear Amplifiers
- Crystal Oscillators

## Pin Configuration



CD4007UB (TOP VIEW)

## Functional Diagram



TERMINAL NO.14- $V_{DD}$   
TERMINAL NO.7- $V_{SS}$

## Absolute Maximum Ratings

Condition	Min	Max	UNITS
DC Supply Voltage Range, ( $V_{DD}$ ) (Voltage Referenced to $V_{SS}$ Terminals)	-0.5	+15	V
Input Voltage Range, All Inputs	-0.5	$V_{DD}+0.5V$	V
DC Input Current, Any One Input	$\pm 10$		mA
Operating Temperature Range	-40	+85	$^{\circ}C$
Storage Temperature Range ( $T_{STG}$ )	-65	+150	$^{\circ}C$
Lead Temperature (During Soldering) At Distance 1/16 $\pm$ 1/32 Inch (1.59mm $\pm$ 0.79mm) from case for 10s Maximum	-	+260	$^{\circ}C$

Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured.

## Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
$V_{DD}$	DC Supply Voltage Range, ( $V_{DD}$ )	3.0	15	V

**Dc Electrical Performance Characteristics**

PARAMETER	SYMBOL	CONDITIONS (NOTE 1)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS	
					MIN	MAX		
Supply Current	I <sub>DD</sub>	V <sub>DD</sub> = 15V, V <sub>IN</sub> = V <sub>DD</sub> or GND	1	+25°C	-	0.5	μA	
			2	+85°C	-	50	μA	
		V <sub>DD</sub> = 15V, V <sub>IN</sub> = V <sub>DD</sub> or GND	3	-40°C	-	0.5	μA	
Input Leakage Current	I <sub>IL</sub>	V <sub>IN</sub> = V <sub>DD</sub> or GND	V <sub>DD</sub> = 15V	1	+25°C	-100	-	nA
			V <sub>DD</sub> =15V	2	+85°C	-1000	-	nA
			V <sub>DD</sub> =15V	3	-40°C	-100	-	nA
Input Leakage Current	I <sub>IH</sub>	V <sub>IN</sub> = V <sub>DD</sub> or GND	V <sub>DD</sub> =15V	1	+25°C	-	100	nA
			V <sub>DD</sub> =15V	2	+85°C	-	1000	nA
			V <sub>DD</sub> =15V	3	-40°C	-	100	nA
Output Voltage	VOL15	V <sub>DD</sub> = 15V, No Load	1, 2, 3	+25°C, +85°C, -40°C	-	50	mV	
Output Voltage	VOH15	V <sub>DD</sub> = 15V, No Load (Note 3)	1, 2, 3	+25°C, +85°C, -40°C	14.95	-	V	
Output Current (Sink)	IOL5	V <sub>DD</sub> = 5V, V <sub>OUT</sub> = 0.4V	1	+25°C	0.53	-	mA	
Output Current (Sink)	IOL10	V <sub>DD</sub> = 10V, V <sub>OUT</sub> = 0.5V	1	+25°C	1.4	-	mA	
Output Current (Sink)	IOL15	V <sub>DD</sub> = 15V, V <sub>OUT</sub> = 1.5V	1	+25°C	3.5	-	mA	
Output Current (Source)	IOH5A	V <sub>DD</sub> = 5V, V <sub>OUT</sub> = 4.6V	1	+25°C	-	-0.53	mA	
Output Current (Source)	IOH5B	V <sub>DD</sub> = 5V, V <sub>OUT</sub> = 2.5V	1	+25°C	-	-1.8	mA	
Output Current (Source)	IOH10	V <sub>DD</sub> = 10V, V <sub>OUT</sub> = 9.5V	1	+25°C	-	-1.4	mA	
Output Current (Source)	IOH15	V <sub>DD</sub> = 15V, V <sub>OUT</sub> = 13.5V	1	+25°C	-	-3.5	mA	
N Threshold Voltage	VNTH	V <sub>DD</sub> = 10V, I <sub>SS</sub> = -10μA	1	+25°C	-2.8	-0.7	V	
P Threshold Voltage	VPTH	V <sub>SS</sub> = 0V, I <sub>DD</sub> = 10μA	1	+25°C	0.7	2.8	V	
Functional	F	V <sub>DD</sub> = 2.8V, V <sub>IN</sub> = V <sub>DD</sub> or GND	7	+25°C	V <sub>OH</sub> > V <sub>DD</sub> /2	V <sub>OL</sub> < V <sub>DD</sub> /2	V	
		V <sub>DD</sub> = 15V, V <sub>IN</sub> = V <sub>DD</sub> or GND	8A	+85°C				
		V <sub>DD</sub> = 3V, V <sub>IN</sub> = V <sub>DD</sub> or GND	8B	-40°C				
Input Voltage Low (Note 2)	VIL	V <sub>DD</sub> = 5V, V <sub>OH</sub> > 4.5V, V <sub>OL</sub> < 0.5V	1, 2, 3	+25°C, +85°C, -40°C	-	1.0	V	
Input Voltage High (Note 2)	VIH	V <sub>DD</sub> = 5V, V <sub>OH</sub> > 4.5V, V <sub>OL</sub> < 0.5V	1, 2, 3	+25°C, +85°C, -40°C	4.0	-	V	
Input Voltage Low (Note 2)	VIL	V <sub>DD</sub> = 15V, V <sub>OH</sub> > 13.5V, V <sub>OL</sub> < 1.5V	1, 2, 3	+25°C, +85°C, -40°C	-	2.5	V	
Input Voltage High (Note 2)	VIH	V <sub>DD</sub> = 15V, V <sub>OH</sub> > 13.5V, V <sub>OL</sub> < 1.5V	1, 2, 3	+25°C, +85°C, -40°C	12.5	-	V	

**NOTES:**

1. All voltages referenced to device GND, 100% testing being implemented.
2. Go/No Go test with limits applied to inputs
3. For accuracy, voltage is measured differentially to V<sub>DD</sub>. Limit is 0.050V max.

**Ac Electrical Performance Characteristics**

PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Propagation Delay	TPHL TPLH	$V_{DD}=5V, V_{IN}=V_{DD}$ or GND	9	+25°C	-	110	ns
			10, 11	+85°C, -40°C	-	149	ns
Transition Time	TTHL TTLH	$V_{DD}=5V, V_{IN}=V_{DD}$ or GND	9	+25°C	-	200	ns
			10, 11	+85°C, -40°C	-	270	ns

**NOTES:**

CL = 50pF, RL = 200K, Input TR, TF < 20ns.

55°C and +85°C limits guaranteed, 100% testing being implemented.

**Electrical Performance Characteristics**

PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Supply Current	IDD	$V_{DD} = 5V, V_{IN} = V_{DD}$ or GND	1, 2	-40°C, +25°C	-	0.25	μA
				+85°C	-	7.5	μA
		$V_{DD}=10V, V_{IN} = V_{DD}$ or GND	1, 2	-40°C, +25°C	-	0.5	μA
				+85°C	-	15	μA
		$V_{DD}=15V, V_{IN} = V_{DD}$ or GND	1, 2	-40°C, +25°C	-	0.5	μA
				+85°C	-	30	μA
Output Voltage	VOL	$V_{DD} = 5V$ , No Load	1, 2	+25°C,+85°C,-40°C	-	50	mV
Output Voltage	VOL	$V_{DD} = 10V$ , No Load	1, 2	+25°C,+85°C,-40°C	-	50	mV
Output Voltage	VOH	$V_{DD} = 5V$ , No Load	1, 2	+25°C,+85°C,-40°C	4.95	-	V
Output Voltage	VOH	$V_{DD} = 10V$ , No Load	1, 2	+25°C,+85°C,-40°C	9.95	-	V
Output Current (Sink)	IOL5	$V_{DD} = 5V, V_{OUT} = 0.4V$	1, 2	+85°C	0.36	-	mA
				-40°C	0.64	-	mA
Output Current (Sink)	IOL10	$V_{DD} = 10V, V_{OUT} = 0.5V$	1, 2	+85°C	0.9	-	mA
				-40°C	1.6	-	mA
Output Current (Sink)	IOL15	$V_{DD} = 15V, V_{OUT} = 1.5V$	1, 2	+85°C	2.4	-	mA
				-40°C	4.2	-	mA
Output Current (Source)	IOH5A	$V_{DD} = 5V, V_{OUT} = 4.6V$	1, 2	+85°C	-	-0.36	mA
				-40°C	-	-0.64	mA
Output Current (Source)	IOH5B	$V_{DD} = 5V, V_{OUT} = 2.5V$	1, 2	+85°C	-	-1.15	mA
				-40°C	-	-2.0	mA
Output Current (Source)	IOH10	$V_{DD} = 10V, V_{OUT} = 9.5V$	1, 2	+85°C	-	-0.9	mA
				-40°C	-	-1.6	mA
Output Current (Source)	IOH15	$V_{DD} = 15V, V_{OUT} = 13.5V$	1, 2	+85°C	-	-2.4	mA
				-40°C	-	-4.2	mA
Input Voltage Low	VIL	$V_{DD}=10V, V_{OH}>9V, V_{OL}<1V$	1, 2	+25°C,+85°C,-40°C	-	2	V
Input Voltage High	VIH	$V_{DD}=10V, V_{OH}>9V, V_{OL}<1V$	1, 2	+25°C,+85°C,-40°C	8	-	V
Propagation Delay	TPHL TPLH	$V_{DD} = 10V$	1, 2, 3	+25°C	-	60	ns
		$V_{DD} = 15V$	1, 2, 3	+25°C	-	50	ns
Transition Time	TTHL TTLH	$V_{DD}=10V$	1, 2, 3	+25°C	-	100	ns
		$V_{DD}=15V$	1, 2, 3	+25°C	-	80	ns
INPUT Capacitance	CIN	Any Input	1, 2	+25°C	-	15.0	pF

**NOTES:**

- All voltages referenced to device GND.
- The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- CL = 50pF, RL = 200K, Input TR, TF < 20ns.

Schematic Diagram

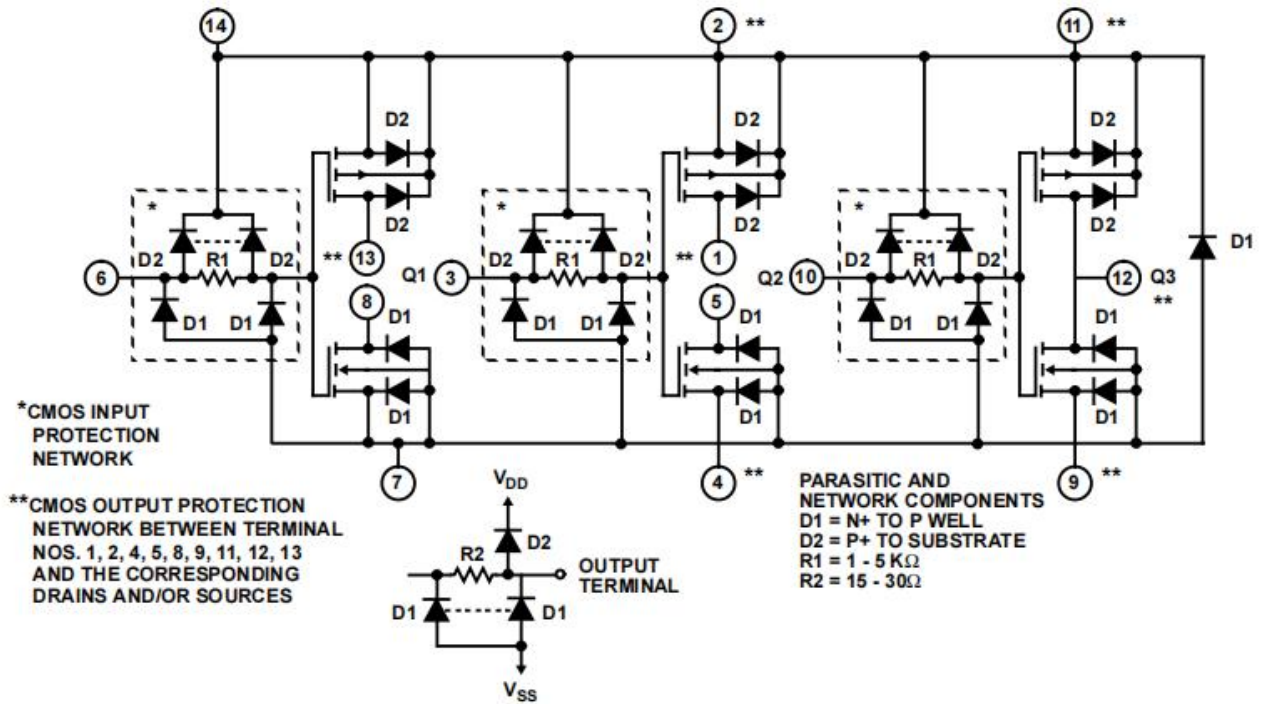
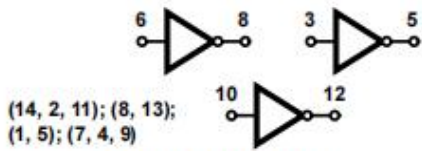
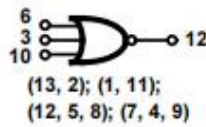


FIGURE 1. DETAILED SCHEMATIC DIAGRAM OF CD4007UB SHOWING INPUT, OUTPUT, AND PARASITIC DIODES

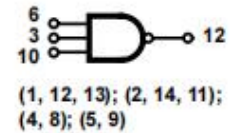
Logic Circuits



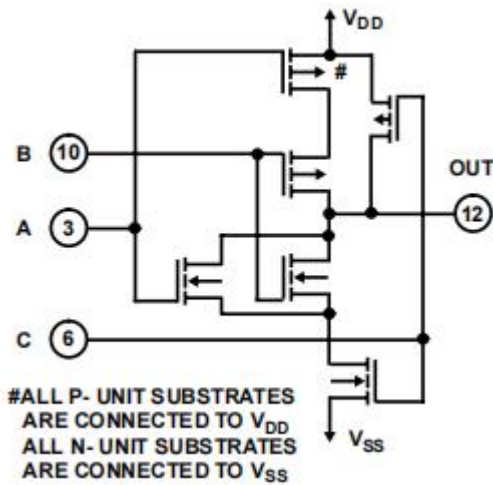
a) TRIPLE INVERTERS



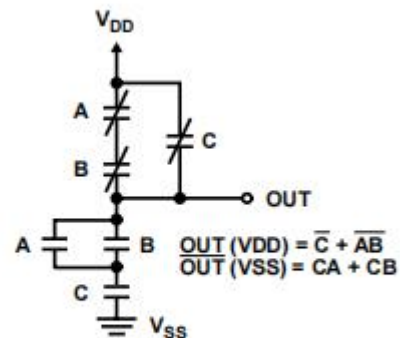
b) 3 - INPUT NOR GATE



c) 3 - INPUT NAND GATE



#ALL P- UNIT SUBSTRATES ARE CONNECTED TO V<sub>DD</sub>  
ALL N- UNIT SUBSTRATES ARE CONNECTED TO V<sub>SS</sub>



(13, 12, 5); (4, 9, 8);  
(14, 2); (1, 11)

d) TREE(RELAY)LOGIC

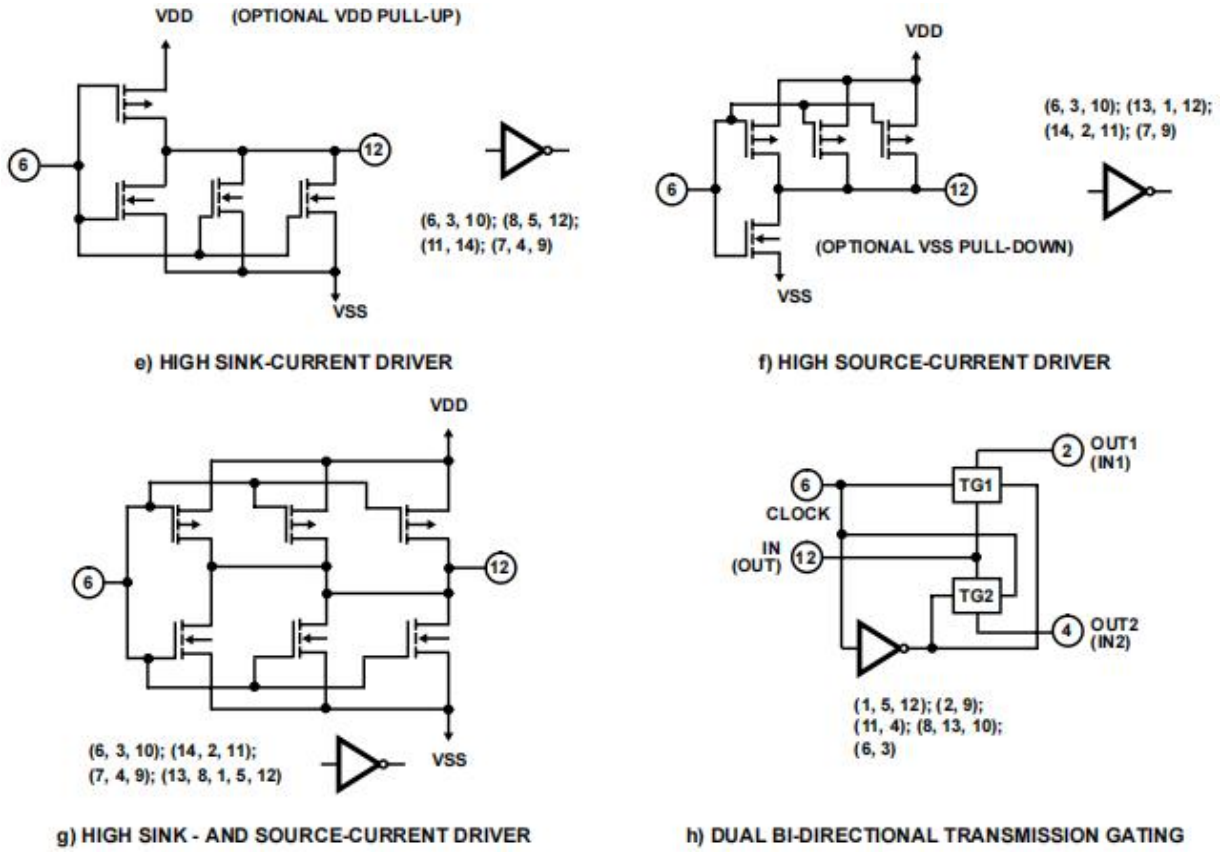


FIGURE 2. SAMPLE CMOS LOGIC CIRCUIT ARRANGEMENTS USING TYPE CD4007UB

Typical Performance Characteristics

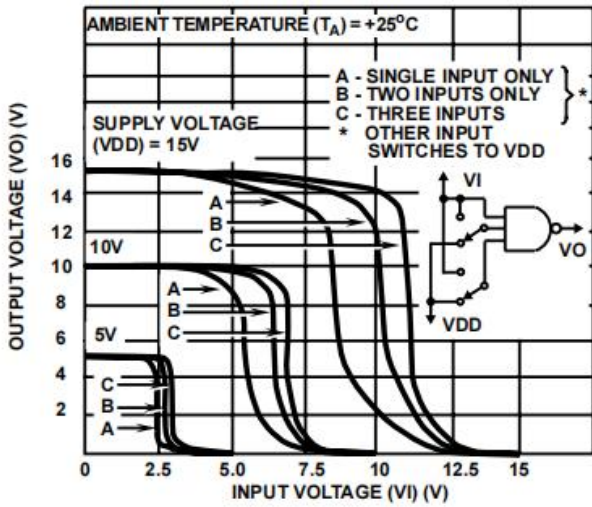


FIGURE 3. TYPICAL VOLTAGE-TRANSFER CHARACTERISTICS FOR NAND GATE

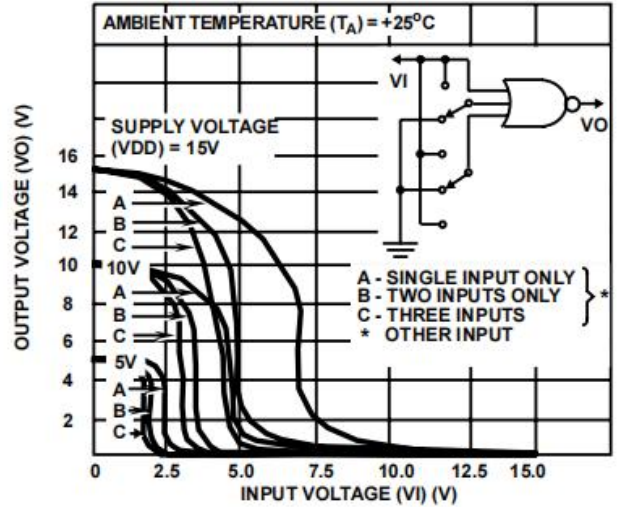


FIGURE 4. TYPICAL VOLTAGE-TRANSFER CHARACTERISTICS FOR NOR GATE

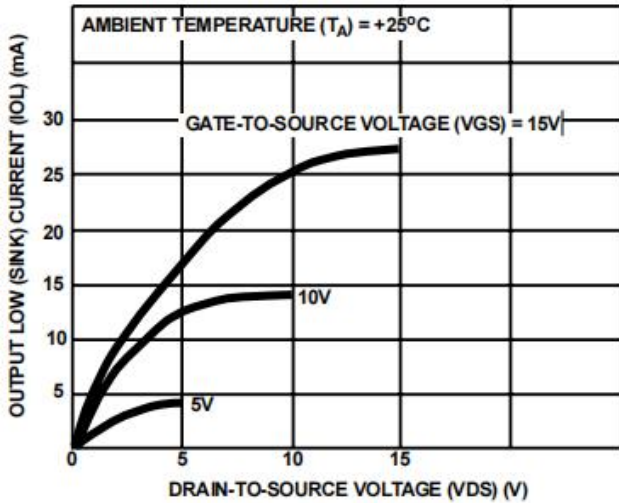


FIGURE 5. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

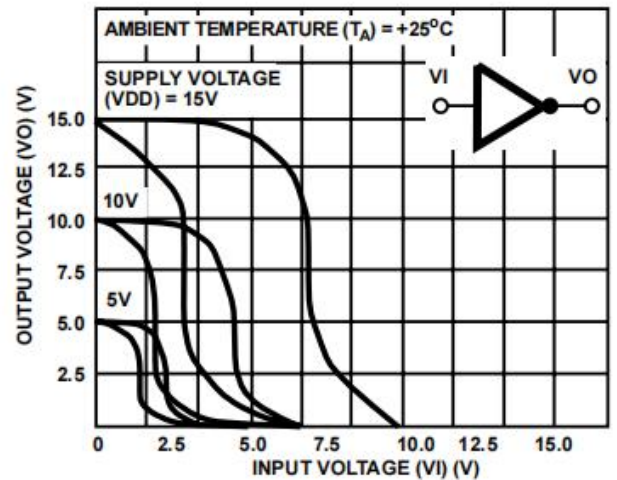


FIGURE 6. MINIMUM AND MAXIMUM VOLTAGE-TRANSFER CHARACTERISTICS FOR INVERTER

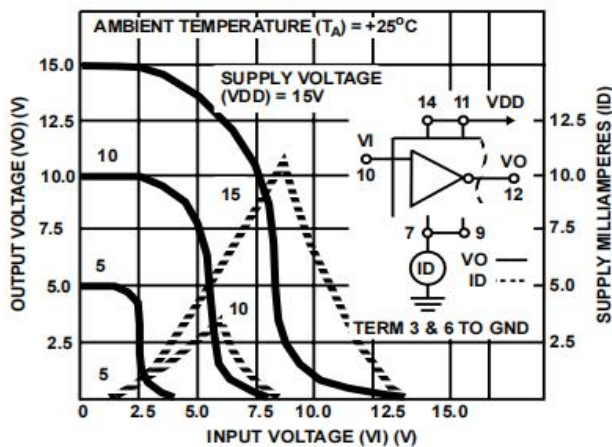


FIGURE 7. TYPICAL CURRENT AND VOLTAGE-TRANSFER CHARACTERISTICS FOR INVERTER

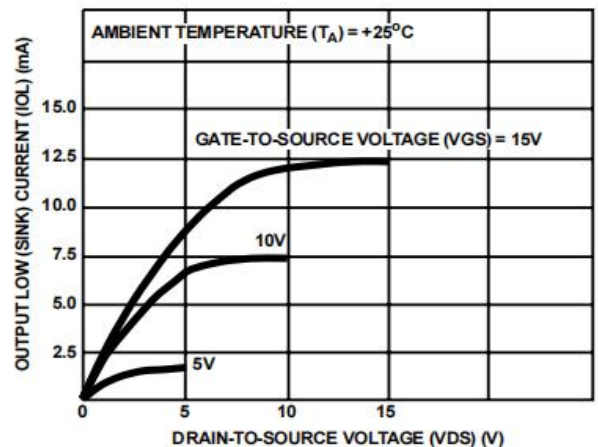


FIGURE 8. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

Typical Performance Characteristics (Continued)

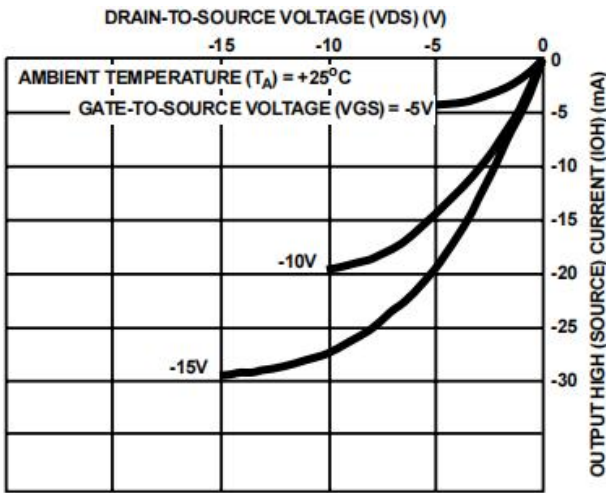


FIGURE 9. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

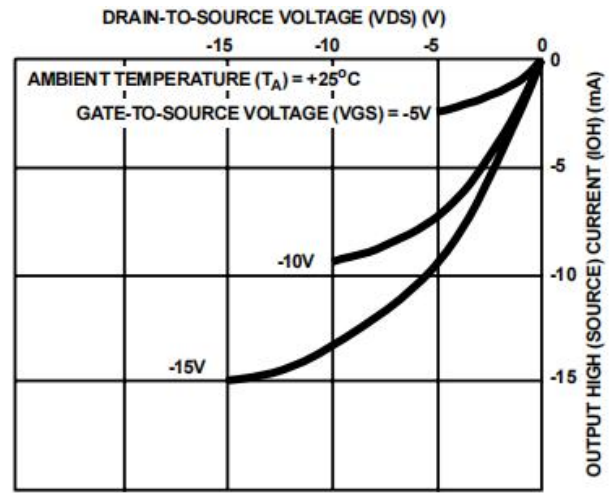


FIGURE 10. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

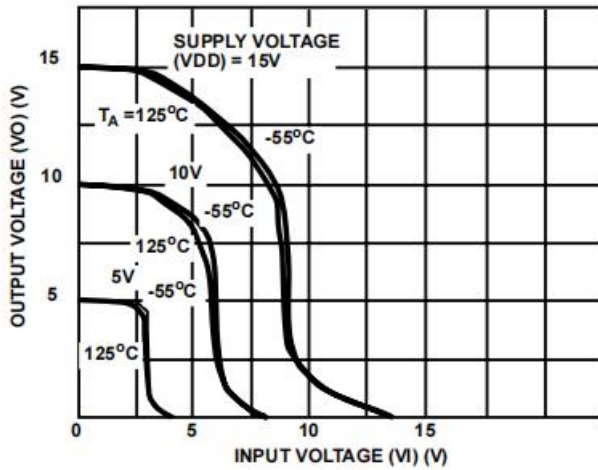


FIGURE 11. TYPICAL VOLTAGE-TRANSFER CHARACTERISTICS AS A FUNCTION OF TEMPERATURE

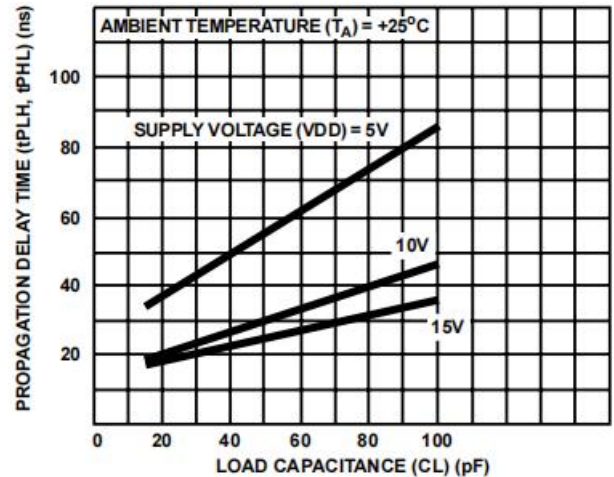


FIGURE 12. TYPICAL PROPAGATION DELAY TIME vs LOAD CAPACITANCE

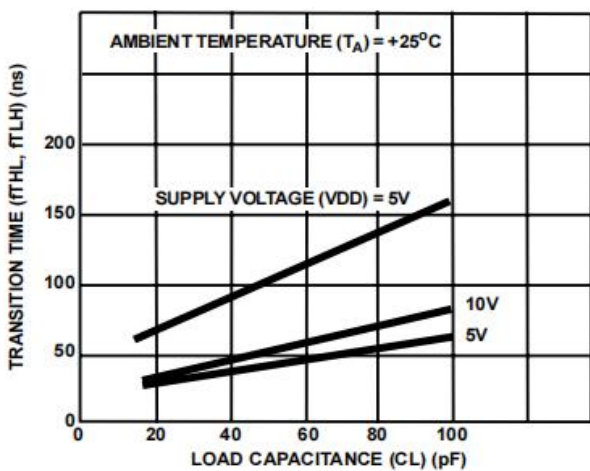


FIGURE 13. TYPICAL TRANSITION TIME vs LOAD CAPACITANCE

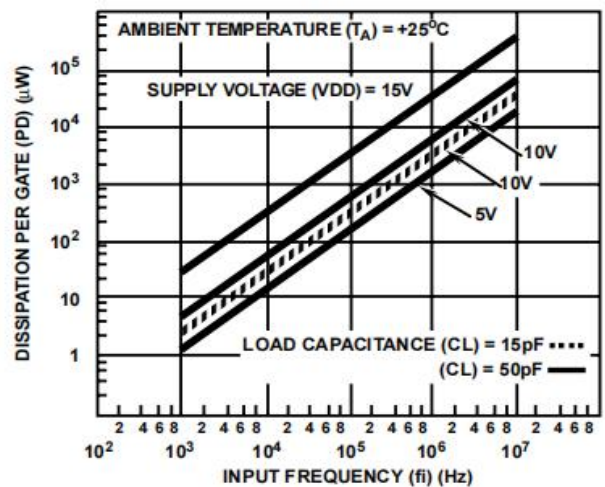
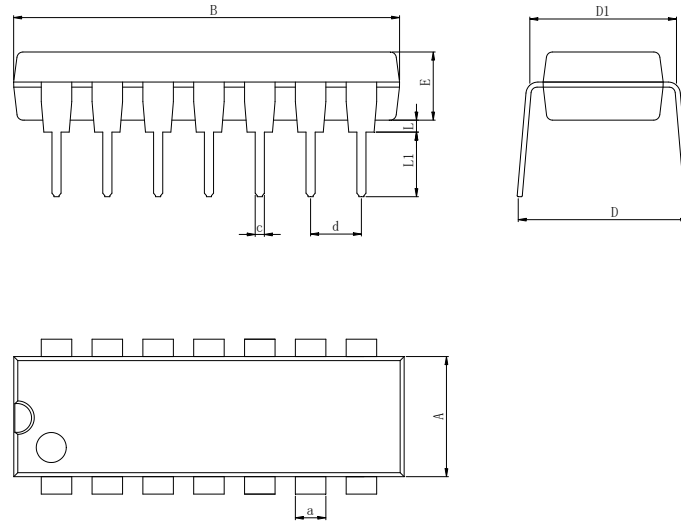


FIGURE 14. TYPICAL DISSIPATION vs FREQUENCY CHARACTERISTICS

## Physical Dimensions

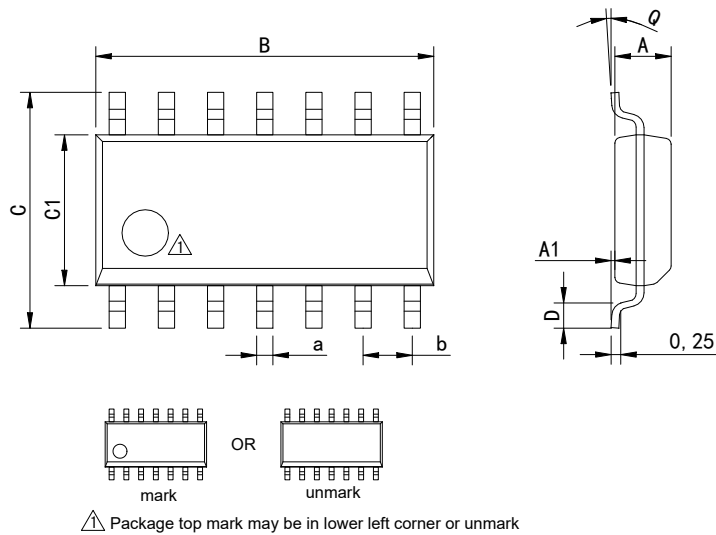
### DIP-14



Dimensions In Millimeters(DIP-14)

Symbol:	A	B	D	D1	E	L	L1	a	c	d
Min:	6.10	18.94	8.10	7.42	3.10	0.50	3.00	1.50	0.40	2.54 BSC
Max:	6.68	19.56	10.9	7.82	3.55	0.70	3.60	1.55	0.50	

### SOP-14

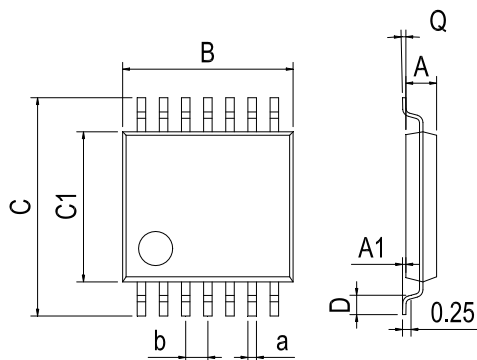


Dimensions In Millimeters(SOP-14)

Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	8.75	6.20	4.00	0.80	8°	0.45	

## Physical Dimensions

TSSOP-14



Dimensions In Millimeters(TSSOP-14)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	

## Revision History

REVISION NUMBER	DATE	REVISION	PAGE
V1.0	2014-6-	New	1-13
V1.1	2017-11	Updated DIP-14 dimension、Add annotation for Maximum Ratings、Update DIP Package New Model	3、 10
V1.2	2020-5	Update encapsulation type	1
V1.3	2024-11	Update Lead Temperature	3
V1.4	2025-11	Update important statements、 Update SOP-14 Dimension drawing	10、 13

---

**IMPORTANT STATEMENT:**

Huaguan Semiconductor reserves the right to change products and services offered without prior notice. Customers should obtain the latest relevant information before placing orders and verify that such information is current and complete. Huaguan Semiconductor assumes no responsibility or liability for altered documents.

Customers are responsible for complying with safety standards and implementing safety measures when using Huaguan Semiconductor products in system design and end-product manufacturing. You assume full responsibility for: selecting the appropriate Huaguan Semiconductor products for your application; designing, validating, and testing your application; and ensuring that your application complies with applicable standards and all other safety, security, or other requirements. This is to prevent potential risks that may lead to personal injury or property damage.

Huaguan Semiconductor products are not approved for use in life support, military, aerospace, or other high-risk applications. Huaguan products are neither intended nor warranted for use in such systems or equipment. Any failure or malfunction may lead to personal injury or severe property damage. Such applications are deemed "Unsafe Use." Unsafe Use includes, but is not limited to: surgical and medical equipment, nuclear energy control equipment, aircraft or spacecraft instruments, control or operation of vehicle power, braking, or safety systems, traffic signal instruments, all types of safety devices, and any other applications intended to support or sustain life. Huaguan Semiconductor shall not be liable for consequences resulting from Unsafe Use in these fields. Users must independently evaluate and assume all risks. Any issues, liabilities, or losses arising from the use of products beyond their approved applications shall be solely borne by the user. Users may not claim any compensation from Huaguan Semiconductor based on these terms. If any third party claims against Huaguan Semiconductor due to such Unsafe Use, the user shall compensate Huaguan Semiconductor for all resulting damages and liabilities.

Huaguan Semiconductor provides technical and reliability data (including datasheets), design resources (including reference designs), application or other design advice, web tools, safety information, and other resources for its semiconductor products. However, no guarantee is made that these resources are free from defects, and no express or implied warranties are provided. The use of testing and other quality control techniques is limited to Huaguan Semiconductor's quality assurance scope. Not all parameters of each device are tested.

Huaguan Semiconductor's documentation authorizes you to use these resources only for developing applications related to the products described herein. You are not granted rights to any other intellectual property of Huaguan Semiconductor or any third party. Any other reproduction or display of these resources is strictly prohibited. You shall fully indemnify Huaguan Semiconductor and its agents against any claims, damages, costs, losses, and liabilities arising from your use of these resources. Huaguan Semiconductor shall not be held responsible.